

# SANYO Semiconductors DATA SHEET

# 2SA2221/2SC6141-

PNP Epitaxial Planar Silicon Transistor NPN Triple Diffused Planar Silicon Transistor

# 230V / 15A, AF100W Output Applications

## **Applications**

· 230V / 15A, AF100W output applications.

#### **Features**

- · Large current capacitance.
- · Wide ASO and high durability against breakdown.
- · Adoption of MBIT process.

Specifications ( ): 2SA2221

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)250	V
Collector-to-Emitter Voltage	VCEO		(-)230	V
Emitter-to-Base Voltage	VEBO		(-)6	V
Collector Current	IC		(-)15	Α
Collector Current (Pulse)	ICP		(-)30	Α
Collector Dissipation	Do		3.5	W
	PC	Tc=25°C	170	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

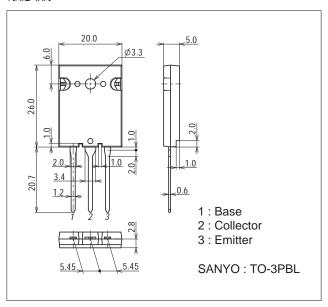
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#### www.Da**Electrical Characteristics** at Ta=25°C

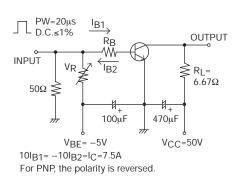
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =(-)250V, I <sub>E</sub> =0A			(-)0.1	mA
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0A			(-)0.1	mA
DC Current Gain	hFE1	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)1A	60		160	
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)7.5A	35			
Gain-Bandwidth Product	fŢ	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)1A		(10)15		MHz
Output Capacitance	Cob	V <sub>CB</sub> =(-)10V, f=1MHz		(400)200		pF
Base-to-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)7.5A			(-)1.5	V
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =(-)7.5A, I <sub>B</sub> =(-)0.75A		(-0.3)0.2	(-)2.0	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=(-)5mA, IE=0A	(-)250			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(-)50mA, R <sub>BE</sub> =∞	(-)230			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =(-)5mA, I <sub>C</sub> =0A	(-)6			V
Turn-On Time	ton	See specified Test Circuit.		(0.45)0.56		μS
Storage Time	tstg	See specified Test Circuit.		(1.75)3.3		μS
Fall Time	tf	See specified Test Circuit.		(0.25)0.4		μS

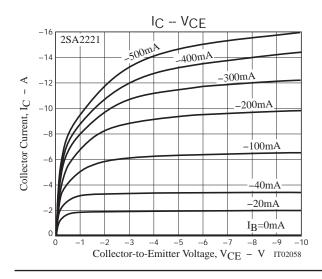
### **Package Dimensions**

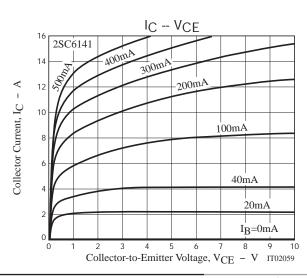
unit : mm (typ) 7502-001

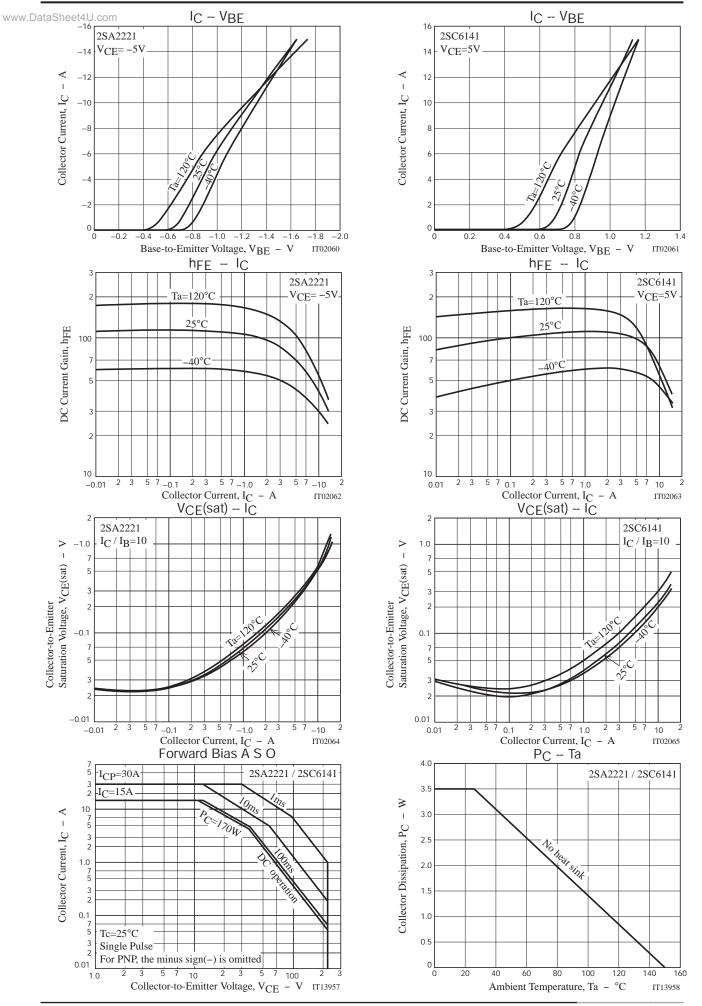


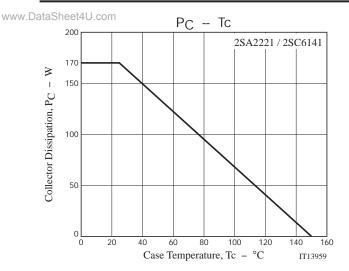
### **Switching Time Test Circuit**











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